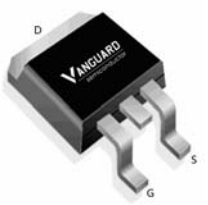
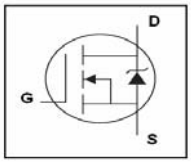
Features

- N-Channel，5V Logic Level Control
- Enhancement mode
- Fast Switching
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- 100% Avalanche test
- Pb-free lead plating; RoHS compliant

V_{DS}	120	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	11.5	mΩ
$R_{DS(on),TYP}$@ V_{GS}=4.5V	13	mΩ
I_D	63	A

TO-263





Part ID	Package Type	Marking	Tape and reel information
VSM012N12MS	TO-263	012N12M	800pcs/Reel

Maximum ratings, at T_j=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
Common Ratings (T_C=25°C Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage		±20	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		120	V
T_J	Maximum Junction Temperature		175	°C
T_{STG}	Storage Temperature Range		-55 to 175	°C
I_S	Diode Continuous Forward Current	T_C=25°C	63	A
Mounted on Large Heat Sink				
I_D	Continuous Drain current@VGS=10V	T_C=25°C	63	A
		T_C=100°C	40	A
I_{DM}	Pulse Drain Current Tested ①	T_C=25°C	240	A
P_D	Maximum Power Dissipation	T_C=25°C	100	W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		1.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		62	°C/W
Drain-Source Avalanche Ratings				
EAS	Avalanche Energy, Single Pulsed ②		56	mJ

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_C = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	120	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V_{DS}=100V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(Tc=125℃)	V_{DS}=100V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.0	2.0	3.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=20A	--	11.5	14	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=4.5V, I_D=10A	--	13.0	16	mΩ
Dynamic Electrical Characteristics @ T_C= 25°C (unless otherwise stated)						
R_g	Gate Resistance	V_{DS}=30V,V_{GS}=0V, f=1MHz	--	1.8	--	Ω
C_{iss}	Input Capacitance		--	3910	--	pF
C_{oss}	Output Capacitance		--	305	--	pF
C_{rss}	Reverse Transfer Capacitance		--	230	--	pF
Q_g	Total Gate Charge	V_{DS}=60V,I_D=30A, V_{GS}=10V	--	54	--	nC
Q_{gs}	Gate-Source Charge		--	13	--	nC
Q_{gd}	Gate-Drain Charge		--	22	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=60V, I_D=20A, R_G=6.8Ω, V_{GS}=10V	--	24	--	nS
t_r	Turn-on Rise Time		--	85	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	55	--	nS
t_f	Turn-Off Fall Time		--	90	--	nS
Source- Drain Diode Characteristics@ T_C = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=20A,V_{GS}=0V	--	0.79	1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=10A, V_{GS}=0V di/dt=100A/μs	--	50	--	nS
Q_{rr}	Reverse Recovery Charge			145		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 15A, V_{GS} =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

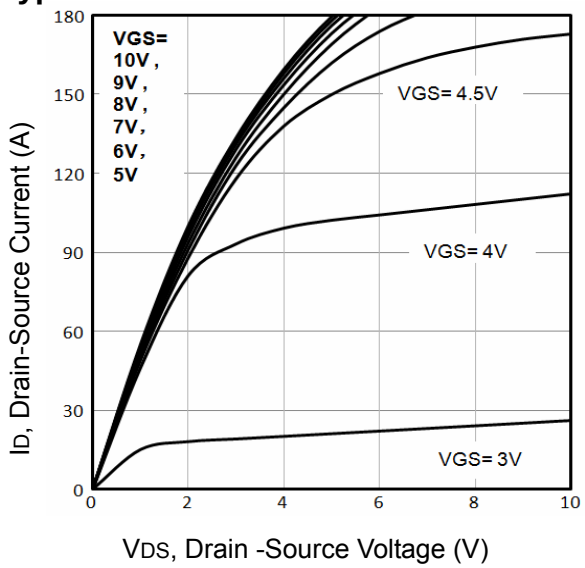


Fig1. Typical Output Characteristics

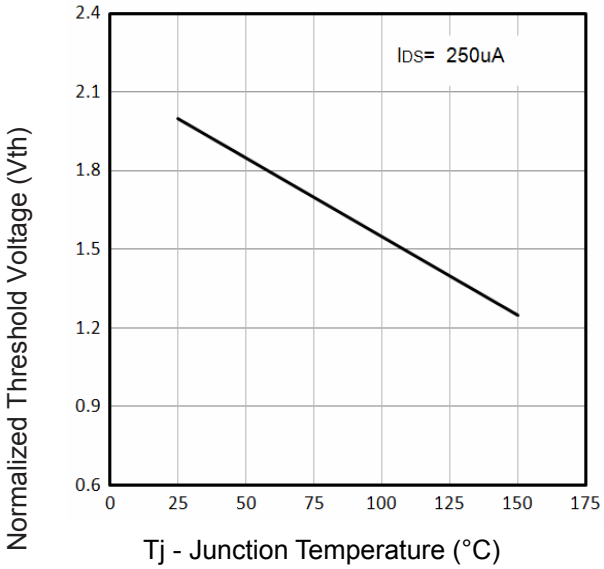


Fig2. Normalized Threshold Voltage Vs. Temperature

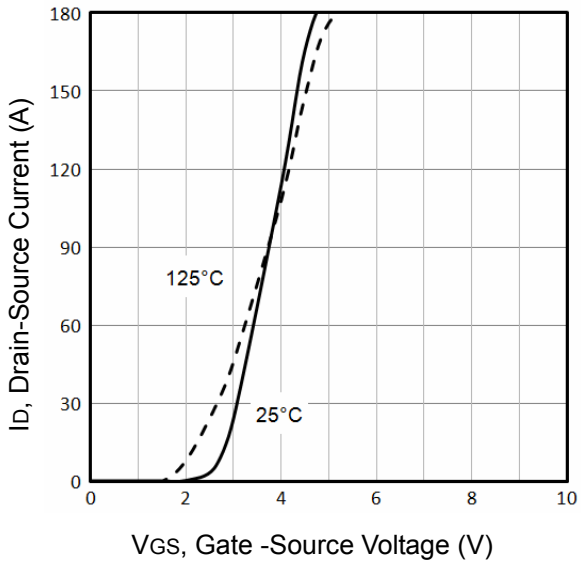


Fig3. Typical Transfer Characteristics

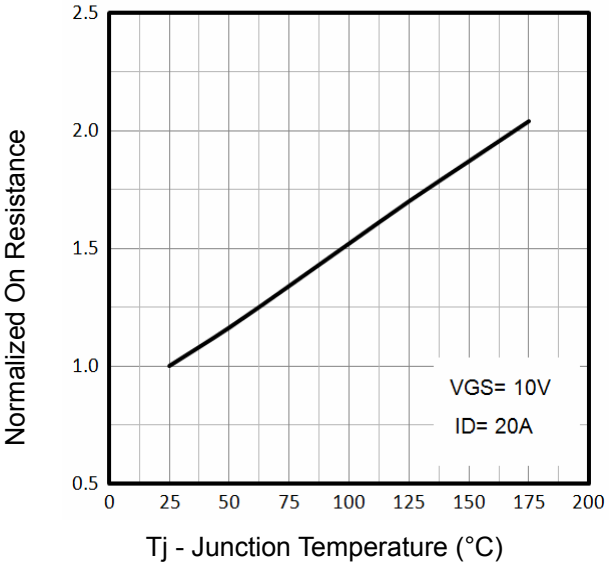


Fig4. Normalized On-Resistance Vs. Temperature

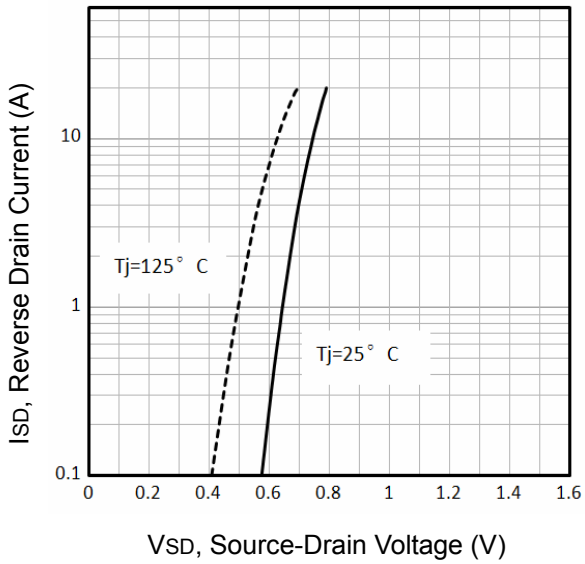


Fig5. Typical Source-Drain Diode Forward Voltage

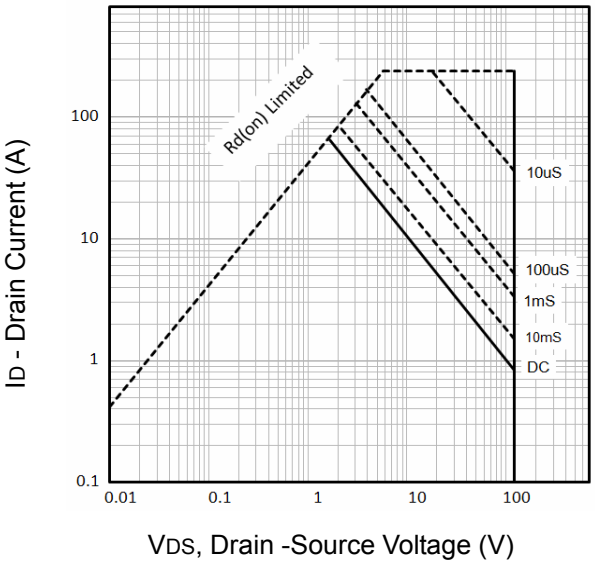


Fig6. Maximum Safe Operating Area

Typical Characteristics

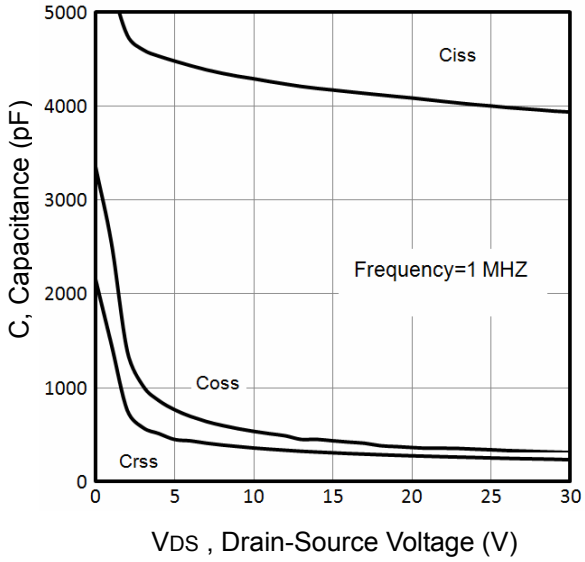


Fig7. Typical Capacitance Vs.Drain-Source

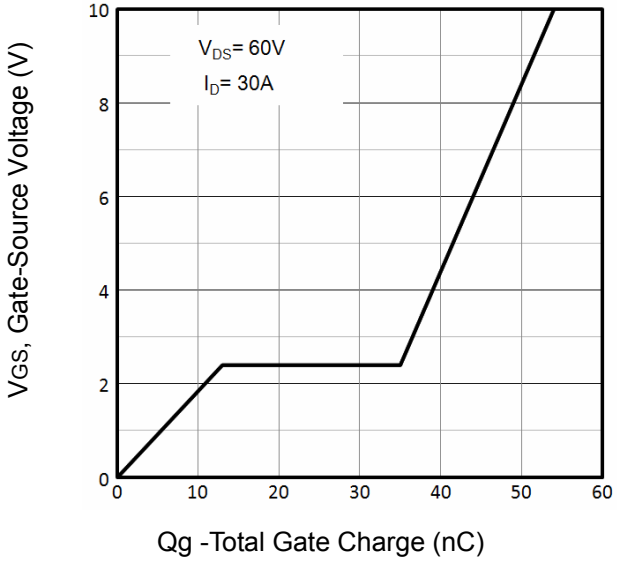


Fig8. Typical Gate Charge Vs.Gate-Source

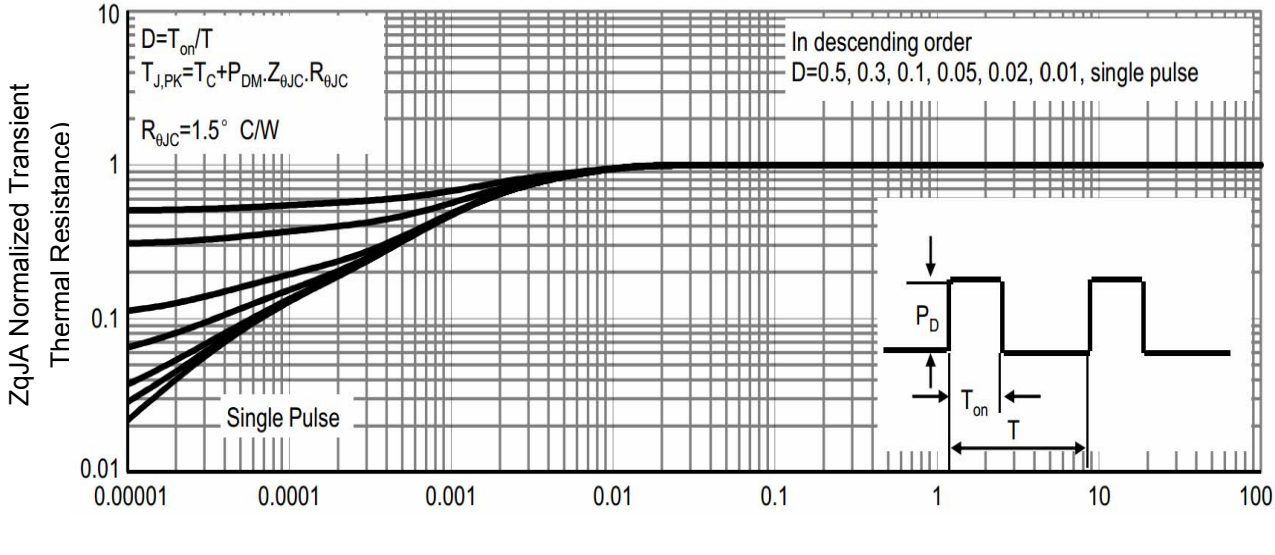


Fig9. Normalized Maximum Transient Thermal Impedance

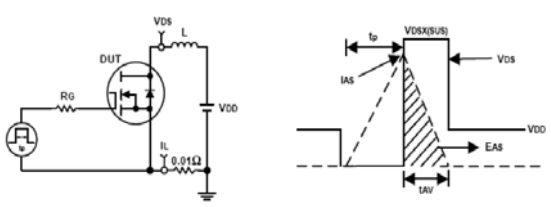


Fig10. Unclamped Inductive Test Circuit and waveforms

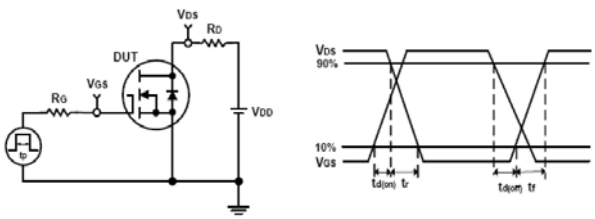
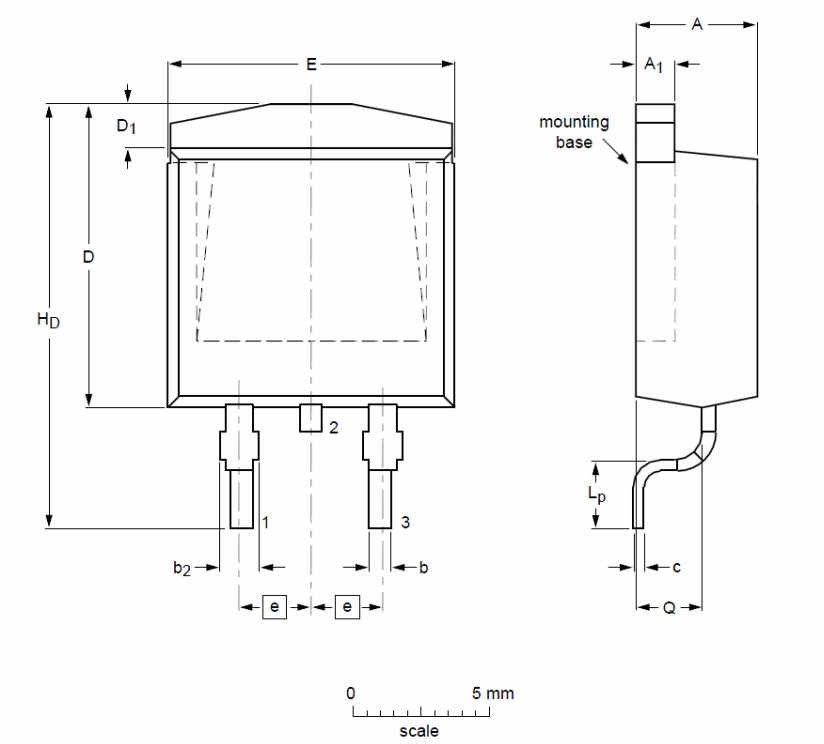


Fig11. Switching Time Test Circuit and waveforms

TO-263 Package Outline Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	4.40	4.55	4.70	**A_1**	1.25	1.30	1.40
b	0.60	0.76	0.85	**b_2**	1.05	1.30	1.45
c	0.35	0.45	0.60	**D**	9.80	10.20	10.50
D_1	1.20	1.51	1.60	**E**	9.70	10.10	10.30
e	--	2.54	--	**H_D**	14.80	15.45	15.80
L_P	2.10	2.40	2.90	**Q**	2.20	2.50	2.60

Customer Service

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